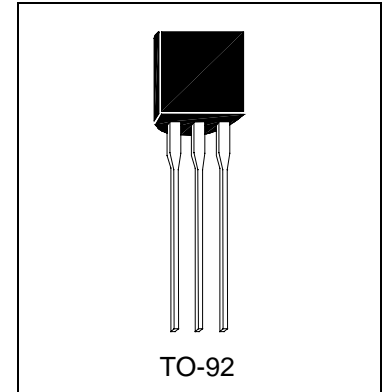




HE8051S

NPN EPITAXIAL PLANAR TRANSISTOR



TO-92

Description

The HE8051S is designed for general purpose amplifier applications.

Absolute Maximum Ratings

- Maximum Temperatures
 - Storage Temperature -55 ~ +150 °C
 - Junction Temperature +150 °C Maximum
- Maximum Power Dissipation
 - Total Power Dissipation (T_A=25°C) 625 mW
- Maximum Voltages and Currents (T_A=25°C)
 - V_{CBO} Collector to Base Voltage 25 V
 - V_{CEO} Collector to Emitter Voltage 20 V
 - V_{EBO} Emitter to Base Voltage 5 V
 - I_C Collector Current 700 mA

Electrical Characteristics (T_A=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CBO}	25	-	-	V	I _C =10uA
BV _{CEO}	20	-	-	V	I _C =1mA
BV _{EBO}	5	-	-	V	I _E =10uA
I _{CBO}	-	-	1	uA	V _{CB} =20V
I _{EBO}	-	-	100	nA	V _{EB} =6V
*V _{CE(sat)}	-	-	0.5	V	I _C =0.5A, I _B =50mA
V _{BE(on)}	-	-	1	V	V _{CE} =1V, I _C =150mA
*h _{FE1}	100	-	500		V _{CE} =1V, I _C =150mA
*h _{FE2}	-	140	-		V _{CE} =1V, I _C =500mA
f _T	150	-	-	MHz	V _{CE} =10V, I _C =20mA, f=100MHz
Cob	-	-	10	pF	V _{CB} =10V, f=1MHz, I _E =0

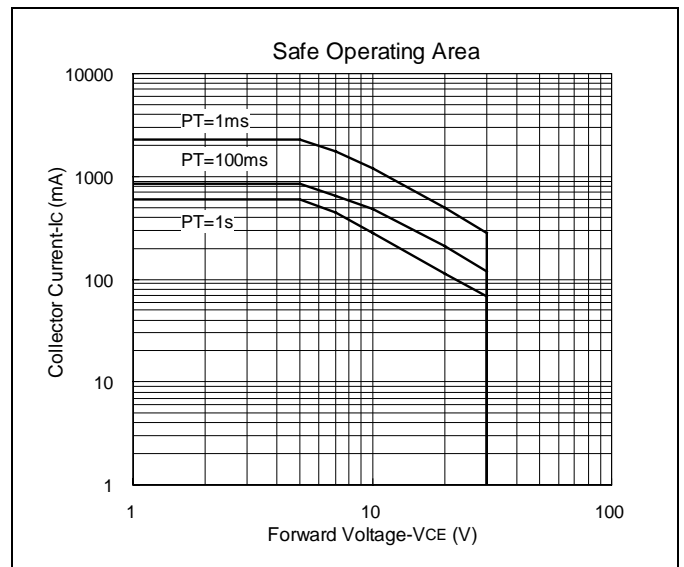
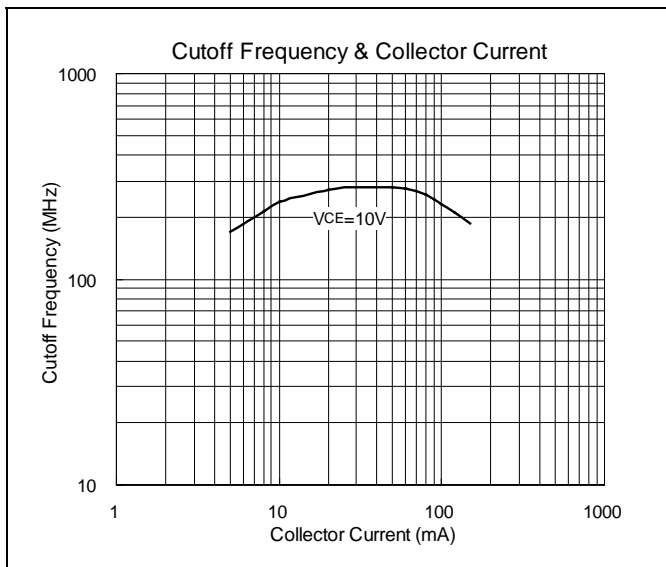
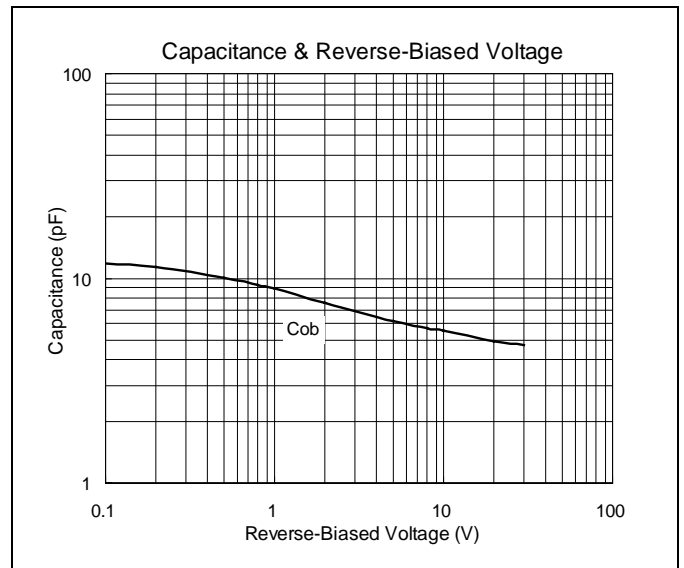
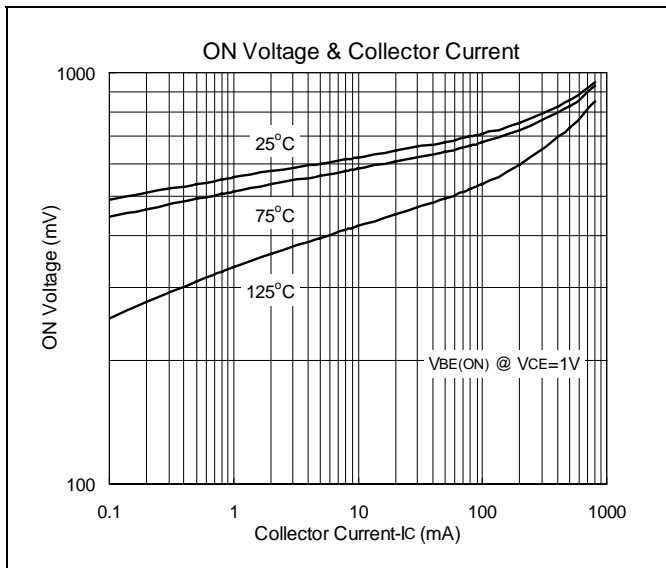
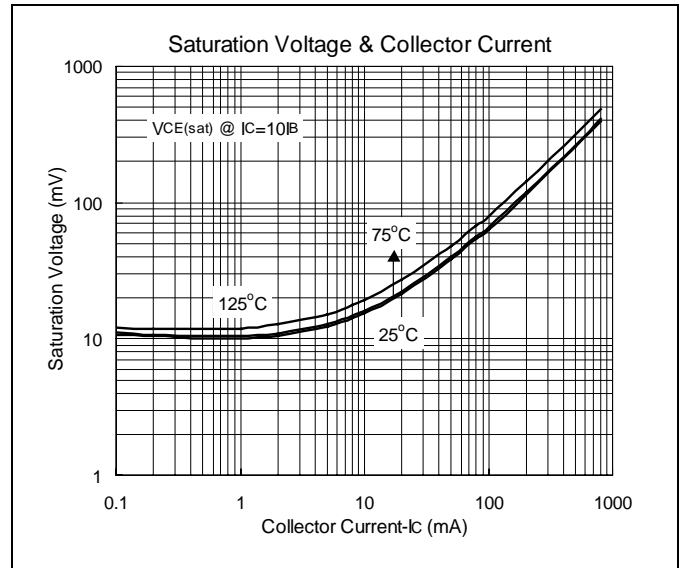
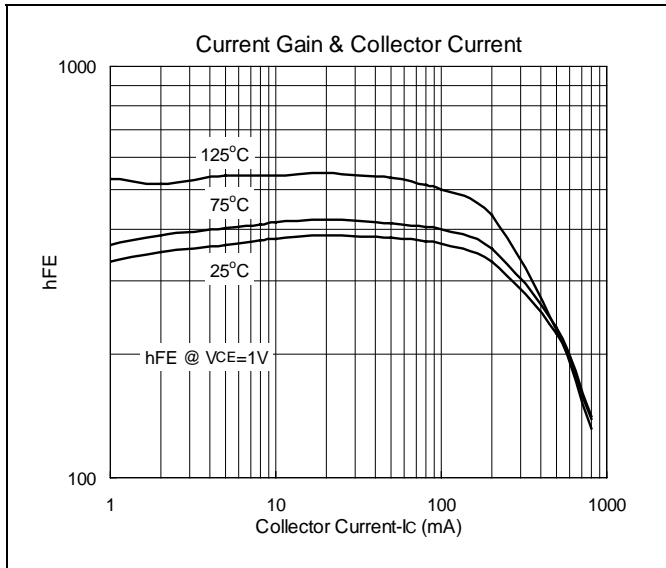
*Pulse Test: Pulse Width ≤380us, Duty Cycle≤2%

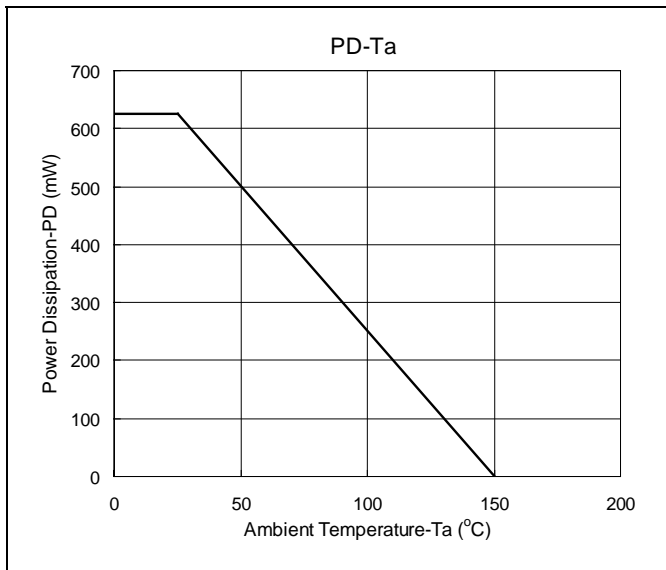
Classification Of hFE

Rank	C	C1	D	D1	E
h _{FE1}	100-200	100-200	160-300	160-300	250-500
h _{FE2}	-	>100	-	>100	-



Characteristics Curve







TO-92 Dimension

3-Lead TO-92 Plastic Package
HSMC Package Code: A

Marking:

Pb Free Mark
 Pb-Free: " * " (Note)
 Normal: None

Date Code Control Code

Note: Green label is used for pb-free packing

Pin Style: 1.Emitter 2.Base 3.Collector

Material:

- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	4.33	4.83
B	4.33	4.83
C	12.70	-
D	0.36	0.56
E	-	*1.27
F	3.36	3.76
G	0.36	0.56
H	-	*2.54
I	-	*1.27
$\alpha 1$	-	*5°
$\alpha 2$	-	*2°
$\alpha 3$	-	*2°

*: Typical, Unit: mm

TO-92 Taping Dimension

DIM	Min.	Max.
A	4.33	4.83
D	3.80	4.20
D1	0.36	0.53
D2	4.33	4.83
F1,F2	2.40	2.90
H	15.50	16.50
H1	8.50	9.50
H2	-	1
H2A	-	1
H3	-	27
H4	-	21
L	-	11
L1	2.50	-
P	12.50	12.90
P1	5.95	6.75
P2	50.30	51.30
T	-	0.55
T1	-	1.42
T2	0.36	0.68
W	17.50	19.00
W1	5.00	7.00

Unit: mm

Important Notice:

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of HSMC.
- HSMC reserves the right to make changes to its products without notice.
- **HSMC semiconductor products are not warranted to be suitable for use in Life-Support Applications, or systems.**
- HSMC assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.

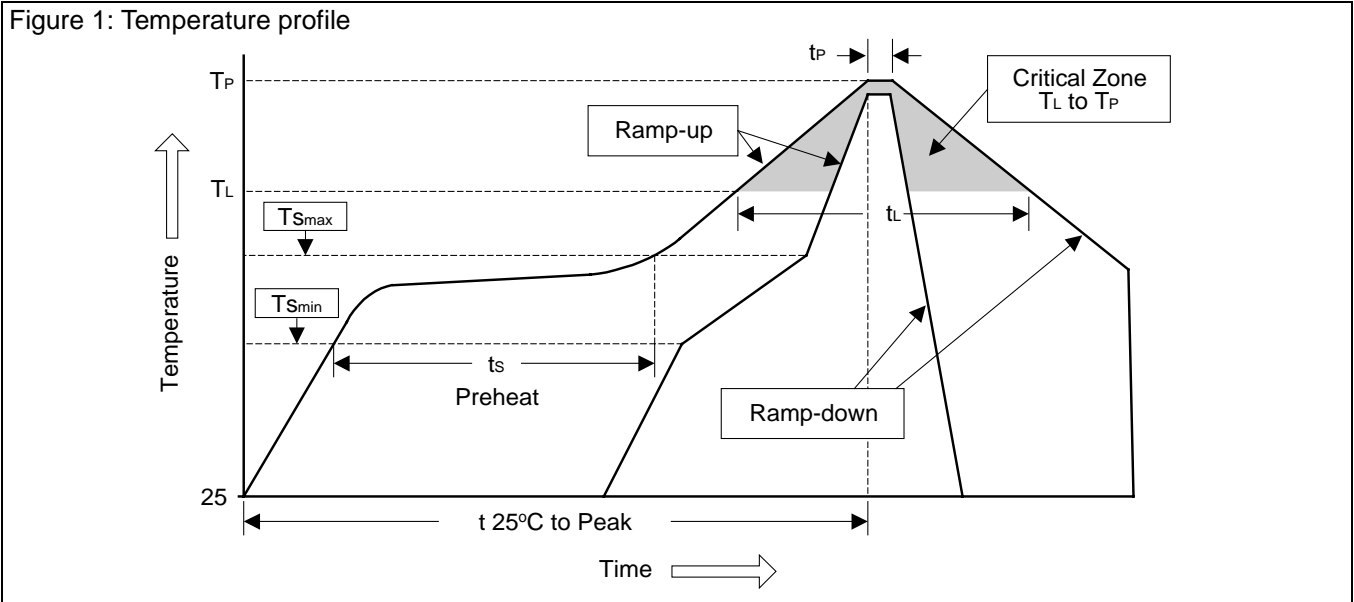
Head Office And Factory:

- **Head Office** (Hi-Sincerity Microelectronics Corp.): 10F.,No. 61, Sec. 2, Chung-Shan N. Rd. Taipei Taiwan R.O.C.
Tel: 886-2-25212056 Fax: 886-2-25632712, 25368454
- **Factory 1:** No. 38, Kuang Fu S. Rd., Fu-Kou Hsin-Chu Industrial Park Hsin-Chu Taiwan. R.O.C
Tel: 886-3-5983621~5 Fax: 886-3-5982931



Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _L to T _p)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (T _{smin})	100°C	150°C
- Temperature Max (T _{smax})	150°C	200°C
- Time (min to max) (ts)	60~120 sec	60~180 sec
T _{smax} to T _L		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T _L)	183°C	217°C
- Time (t _L)	60~150 sec	60~150 sec
Peak Temperature (T _p)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t _p)	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec